ABSTRACT

Disclosed is a light-emitting device (100) has a light-emitting layer portion (24) which is composed of a group III-V compound semiconductor and a transparent thick-film semiconductor layer (90) with a thickness of not less than 40 μm which is formed on at least one major surface side of the light-emitting layer portion (24) and composed of a group III-V compound semiconductor having a band gap energy larger than the photon energy equivalent of the peak wavelength of emission flux from the light-emitting layer portion (24). The transparent thick-film semiconductor layer (90) has a lateral surface portion (90S) which is a chemically etched surface. The dopant concentration of the transparent thick-film semiconductor layer (90) is not less than 5 X $10^{16}/cm^3$ and not more than 2 x $10^{18}/cm^3$. The light-emitting device can have a transparent thick-film semiconductor layer while being significantly improved in light taking-out efficiency from the lateral surface portion.